BPW76A, BPW76B

Vishay Semiconductors



Silicon NPN Phototransistor, RoHS Compliant



BPW76 is a silicon NPN phototransistor with high radiant

sensitivity in hermetically sealed TO-18 package with base

terminal and flat glass window. It is sensitive to visible and

FEATURES

- Package type: leaded
- Package form: TO-18
- Dimensions (in mm): Ø 4.7
- · High photo sensitivity
- High radiant sensitivity
- · Suitable for visible and near infrared radiation
- · Fast response times
- Angle of half sensitivity: $\phi = \pm 40^{\circ}$
- · Base terminal connected
- Hermetically sealed package
- Flat glass window
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

· Detector in electronic control and drive circuits

PRODUCT SUMMARY COMPONENT I_{ca} (mA) φ (deg) λ_{0.1} (nm) BPW76A 0.4 to 0.8 ± 40 450 to 1080 BPW76B > 0.6 ± 40 450 to 1080

Note

DESCRIPTION

near infrared radiation.

Test condition see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING REMARKS PACKAGE				
BPW76A	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18		
BPW76B	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18		

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Collector base voltage		V _{CBO}	80	V	
Collector emitter voltage		V _{CEO}	70	V	
Emitter base voltage		V _{EBO}	5	V	
Collector current		Ι _C	50	mA	
Collector peak current	$t_p/T=0.5,t_p\leq 10\;ms$	I _{CM}	100	mA	
Total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	Pv	250	mW	
Junction temperature		Tj	125	°C	
Operating temperature range		T _{amb}	- 40 to + 125	°C	
Storage temperature range		T _{stg}	- 40 to + 125	°C	
Soldering temperature	$t \le 5 s$	T _{sd}	260	°C	
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R _{thJA}	400	K/W	
Thermal resistance junction/gase		R _{thJC}	150	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified

COMPLIANT



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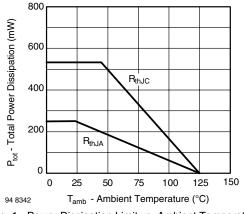


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	70			V
Collector emitter dark current	$V_{CE} = 20 V, E = 0$	I _{CEO}		1	100	nA
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}		6		pF
Angle of half sensitivity		φ		± 40		deg
Wavelength of peak sensitivity		λ _p		850		nm
Range of spectral bandwidth		λ _{0.1}		450 to 1080		nm
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$, $I_C = 0.1 \text{ mA}$	V _{CEsat}		0.15	0.3	V
Turn-on time	V_{S} = 5 V, I_{C} = 5 mA, R_{L} = 100 Ω	t _{on}		6		μs
Turn-off time	V_{S} = 5 V, I_{C} = 5 mA, R_{L} = 100 Ω	t _{off}		5		μs
Cut-off frequency	V_S = 5 V, I_C = 5 mA, R_L = 100 Ω	fc		110		kHz

Note

T_{amb} = 25 °C, unless otherwise specified

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector light ourrent	$\label{eq:eq:energy} \begin{split} E_{e} = 1 \ mW/cm^2, \lambda = 950 \ nm, \\ V_{CE} = 5 \ V \end{split}$	BPW76A	I _{ca}	0.4		0.8	mA
Collector light current		BPW76B	I _{ca}	0.6			mA

BASIC CHARACTERISTICS

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

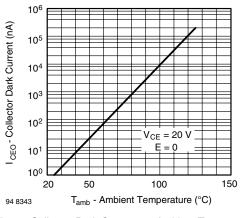


Fig. 2 - Collector Dark Current vs. Ambient Temperature

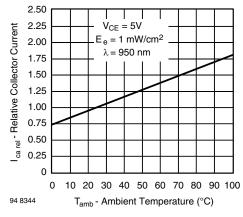


Fig. 3 - Relative Collector Current vs. Ambient Temperature

For technical questions, contact: detectortechsupport@vishay.com

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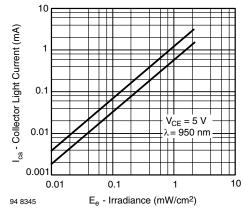


Fig. 4 - Collector Light Current vs. Irradiance

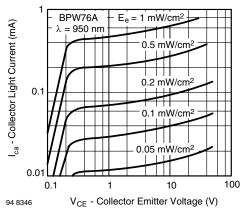


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

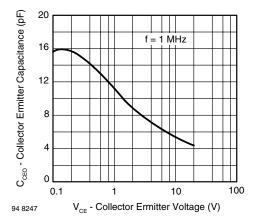


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

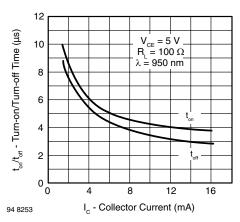


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

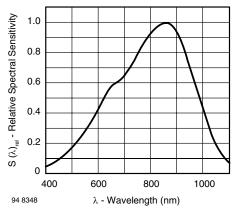


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

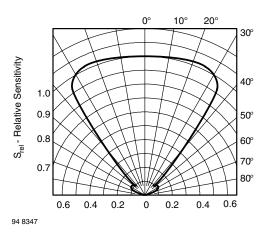


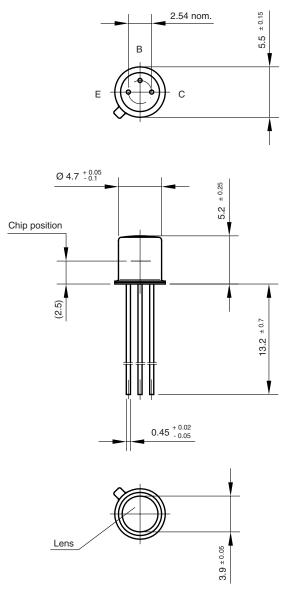
Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement

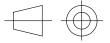


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PACKAGE DIMENSIONS in millimeters





technical drawings according to DIN specifications

Drawing-No.: 6.503-5004.01-4 Issue:1; 01.07.96 96 12175



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